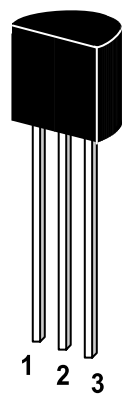


ST 2N2907 / 2N2907A

PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into one group according to its DC current gain. As complementary type the NPN transistor ST 2N2222 and ST 2N2222A are recommended.

On special request, these transistors can be manufactured in different pin configurations.

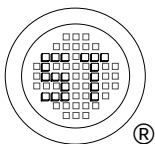


1. Emitter 2. Base 3. Collector

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value		Unit
		ST 2N2907	ST 2N2907A	
Collector Base Voltage	-V _{CBO}	60		V
Collector Emitter Voltage	-V _{CEO}	40	60	V
Emitter Base Voltage	-V _{EBO}	5		V
Collector Current	-I _C	600		mA
Power Dissipation	P _{tot}	625		mW
Junction Temperature	T _j	150		°C
Storage Temperature Range	T _s	-55 to +150		°C



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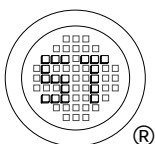


Dated : 23/12/2005

ST 2N2907 / 2N2907A

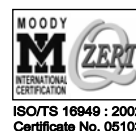
Characteristics at $T_a = 25^\circ\text{C}$

Parameter		Symbol	Min.	Max.	Unit
DC Current Gain	at $-I_C = 0.1\text{ mA}$, $-V_{CE} = 10\text{ V}$	ST 2N2907	h_{FE}	35	-
		ST 2N2907A	h_{FE}	75	-
	at $-I_C = 1\text{ mA}$, $-V_{CE} = 10\text{ V}$	ST 2N2907	h_{FE}	50	-
		ST 2N2907A	h_{FE}	100	-
	at $-I_C = 10\text{ mA}$, $-V_{CE} = 10\text{ V}$	ST 2N2907	h_{FE}	75	-
		ST 2N2907A	h_{FE}	100	-
	at $-I_C = 150\text{ mA}$, $-V_{CE} = 10\text{ V}$		h_{FE}	100	300
	at $-I_C = 500\text{ mA}$, $-V_{CE} = 10\text{ V}$	ST 2N2907	h_{FE}	30	-
		ST 2N2907A	h_{FE}	50	-
Collector Cutoff Current	at $-V_{CB} = 50\text{ V}$	ST 2N2907	$-I_{CBO}$	-	nA
		ST 2N2907A	$-I_{CBO}$	10	nA
Collector Base Breakdown Voltage	at $-I_C = 10\text{ }\mu\text{A}$		$-V_{(BR)CBO}$	60	V
Collector Emitter Breakdown Voltage	at $-I_C = 10\text{ mA}$	ST 2N2907	$-V_{(BR)CEO}$	40	V
		ST 2N2907A	$-V_{(BR)CEO}$	60	V
Emitter Base Breakdown Voltage	at $-I_E = 10\text{ }\mu\text{A}$		$-V_{(BR)EBO}$	5	V
Collector Saturation Voltage	at $-I_C = 150\text{ mA}$, $-I_B = 15\text{ mA}$		$-V_{CE(sat)}$	0.4	V
	at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$		$-V_{CE(sat)}$	1.6	V
Base Saturation Voltage	at $-I_C = 150\text{ mA}$, $-I_B = 15\text{ mA}$		$-V_{BE(sat)}$	1.3	V
	at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$		$-V_{BE(sat)}$	2.6	V
Gain Bandwidth Product	at $-I_C = 50\text{ mA}$, $-V_{CE} = 20\text{ V}$, $f = 100\text{ MHz}$		f_T	200	MHz
Collector Output Capacitance	at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$		C_{ob}	8	pF
Input Capacitance	at $-V_{BE} = 2\text{ V}$, $f = 1\text{ MHz}$		C_{ib}	30	pF



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